[EQUATION 1]

$$\{101\} \text{ ORIENTATION RATIO} = \frac{\text{NUMBER OF MEASURED POINTS WITHIN ALLOWABLE ANGLE BETWEEN LATTICE PLANE }\{101\}\text{ AND FILM SURFACE}}{\text{TOTAL NUMBER OF MEASURED POINTS}}$$

[TABLE 1]

ITEMS		FIRST AMORPHOUS SEMICONDUCTOR FILM	SECOND AMORPHOUS SEMICONDUCTOR FILM
SiH₄ FLOW AMOUNT	[sccm]	$50 \sim 95$	100
GeH₄(H₂-BASE 10%) FLOW AMOUNT	[sccm]	$50 \sim 5$	0
RF POWER	[W/cm²]	0.35	←
PULSE FREQUENCY	[KHz]	10	←
DUTY	[%]	30	←
PRESSURE	[Pa]	33.25	←
SUBSTRATE TEMPERATURE (Tsub)	[°C]	300	←
ELECTRODE GAP (GAP)	[mm]	35	←